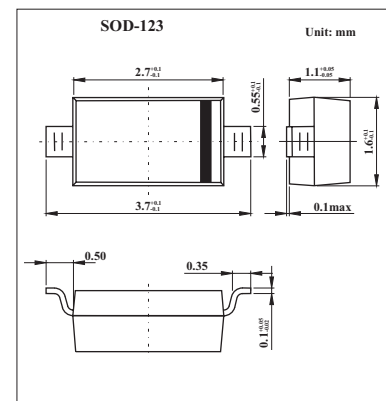


Silicon Schottky Barrier Diode

HSU88

■ Features

- Low capacitance. (C=0.8pF max)
- Low forward voltage.
- Ultra small Resin Package (URP) is suitable for high density surface mounting and high speed assembly.



■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Value	Unit
Reverse Voltage	V _R	10	V
Average rectified current	I _O	15	mA
Junction temperature	T _j	125	°C
Storage temperature	T _{stg}	-55 to +125	°C

■ Electrical Characteristics Ta = 25 °C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	V _F	I _F = 1 mA	350		420	mV
		I _F = 10 mA	500		580	
Reverse current	I _R	V _R = 2 V			0.2	μ A
		V _R = 10 V			10	
Capacitance	C	V _R = 0 V, f = 1 MHz			0.8	pF
ESD-Capability (Note 1)		C = 200pF, Both forward and reverse direction 1 pulse.	30			V

Note

1. Failure criterion ; I_R ≥ 400 nA at V_R = 2 V

■ Marking

Marking	9
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